L Number	Hits	Search Text	DB	Time stamp
2	448476	offset	USPAT; US-PGPUB; JPO	2004/09/28 16:13
4	196762	cmp or polish$3	USPAT; US-PGPUB; JPO	2004/09/28 16:54
5	79439	polysilicon	USPAT; US-PGPUB; JPO	2004/09/28 16:16
6	357183	plug$1	USPAT; US-PGPUB; JPO	2004/09/28 16:16
7	558	(cmp or polish$3) with polysilicon with plug$1	USPAT; US-PGPUB; JPO	2004/09/28 16:16
8	1246677	vertical	USPAT; US-PGPUB; JPO	2004/09/28 16:55
9	612815	gate$1	USPAT; US-PGPUB; JPO	2004/09/28 16:55
10	903961	channel$1	USPAT; US-PGPUB; JPO	2004/09/28 16:55
11	169053	drain same source	USPAT; US-PGPUB; JPO	2004/09/28 16:55
12	54245	vertical and gate$1 and channel$1	USPAT; US-PGPUB; JPO	2004/09/28 16:55
13	11722	(drain same source) and (vertical and gate$1 and channel$1) and polysilicon	USPAT; US-PGPUB; JPO	2004/09/28 16:57
14	14430	vertical with (transistor$1)	USPAT; US-PGPUB; JPO	2004/09/28 16:57
15	3582	((drain same source) and (vertical and gate$1 and channel$1) and polysilicon) and (vertical with (transistor$1))	USPAT; US-PGPUB; JPO	2004/09/28 16:57
16	360468	etch$3	USPAT; US-PGPUB; JPO	2004/09/28 16:57
17	2858	(((drain same source) and (vertical and gate$1 and channel$1) and polysilicon) and (vertical with (transistor$1))) and etch$3	USPAT; US-PGPUB; JPO	2004/09/28 16:58
18	2529	diffus$3 same heat$3 same (drain same source) same (dopant$1 or impurity or impurities)	USPAT; US-PGPUB; JPO	2004/09/28 16:59
19	137	((((drain same source) and (vertical and gate$1 and channel$1) and polysilicon) and (vertical with (transistor$1))) and etch$3) and (diffus$3 same heat$3 same (drain same source) same (dopant$1 or impurity or impurities))	USPAT; US-PGPUB; JPO	2004/09/28 16:59

C:\APPS\east\workspaces\~~ACOLLECTIONSEARCH-ALLOW-01.wsp

L Number	Hits	Search Text	DB	Time stamp
1	1055	mosfet$1 with jfet$1	USPAT; US-PGPUB; JPO	2004/09/28 20:08
2	80942	gate adj (oxide or dielectric or insulat$3)	USPAT; US-PGPUB; JPO	2004/09/28 19:15
3	461	"without" adj2 (gate adj (oxide or dielectric or insulat$3))	USPAT; US-PGPUB; JPO	2004/09/28 19:15
4	0	(mosfet$1 with jfet$1) and ("without" adj2 (gate adj (oxide or dielectric or insulat$3)))	USPAT; US-PGPUB; JPO	2004/09/28 19:20
5	41	(mosfet$1 with jfet$1) same (gate adj (oxide or dielectric or insulat$3))	USPAT; US-PGPUB; JPO	2004/09/28 19:50
7	6219	vertical near2 (transistor$1)	USPAT; US-PGPUB; JPO	2004/09/28 20:10
8	6169	jfet$1 or (junction-fet$1) or (junction adj fet$1) or (junction adj field adj effect)	USPAT; US-PGPUB; JPO	2004/09/28 19:51
9	120	(vertical near2 (transistor$1)) same (jfet$1 or (junction-fet$1) or (junction adj fet$1) or (junction adj field adj effect))	USPAT; US-PGPUB; JPO	2004/09/28 20:02
13	150893	mosfet$1 or mos or (metal adj oxide adj semiconduct$3)	USPAT; US-PGPUB; JPO	2004/09/28 20:10
14	2121	(jfet$1 or (junction-fet$1) or (junction adj fet$1) or (junction adj field adj effect)) same (mosfet$1 or mos or (metal adj oxide adj semiconduct$3))	USPAT; US-PGPUB; JPO	2004/09/28 20:10
15	164	(vertical near2 (transistor$1)) and ((jfet$1 or (junction-fet$1) or (junction adj fet$1) or (junction adj field adj effect)) same (mosfet$1 or mos or (metal adj oxide adj semiconduct$3)))	USPAT; US-PGPUB; JPO	2004/09/28 20:10
16	80	((vertical near2 (transistor$1)) and ((jfet$1 or (junction-fet$1) or (junction adj fet$1) or (junction adj field adj effect)) same (mosfet$1 or mos or (metal adj oxide adj semiconduct$3)))) not (((mosfet$1 with jfet$1) same (gate adj (oxide or dielectric or insulat$3))) or ((vertical near2 (transistor$1)) same (jfet$1 or (junction-fet$1) or (junction adj fet$1) or (junction adj field adj effect))))	USPAT; US-PGPUB; JPO	2004/09/28 20:10